

# MM54HC4016/MM74HC4016 Quad Analog Switch

#### **General Description**

These devices are digitally controlled analog switches implemented in advanced silicon-gate CMOS technology. These switches have low "on" resistance and low "off" leakages. They are bidirectional switches, thus any analog input may be used as an output and vice-versa. The '4016 devices allow control of up to 12V (peak) analog signals with digital control signals of the same range. Each switch has its own control input which disables each switch when low. All analog inputs and outputs and digital inputs are protected from electrostatic damage by diodes to V<sub>CC</sub> and ground

#### **Features**

- Typical switch enable time: 15 ns
- Wide analog input voltage range: 0-12V
- Low "on" resistance:  $50\Omega$  typ.
- Low quiescent current: 80 µA maximum (74HC)
- Matched switch characteristics
- Individual switch controls

#### **Connection Diagram**

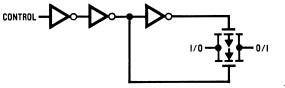
# Dual-In-Line Package VCC 1CTL 4CTL 4I/0 40/I 30/I 3I/0 14 13 12 11 10 9 8 1 1 2 3 4 5 6 7 1I/0 10/I 20/I 2I/0 2CTL 3CTL GND TL/F/5350-1 Top View

#### Order Number MM54HC4016 or MM74HC4016

#### **Truth Table**

Input	Switch
CTL	1/0-0/1
L	"OFF"
Н	"ON"

#### **Schematic Diagram**



#### Absolute Maximum Ratings (Notes 1 & 2) If Military/Aerospace specified devices are required,

please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V <sub>CC</sub> )	-0.5  to  + 15 V
DC Control Input Voltage (VIN)	$-1.5$ to $V_{CC} + 1.5V$
DC Switch I/O Voltage (V <sub>IO</sub> )	$-0.5$ to $V_{CC} + 0.5V$
Clamp Diode Current (I <sub>IK</sub> , I <sub>OK</sub> )	$\pm$ 20 mA
DC Output Current, per pin (I <sub>OUT</sub> )	$\pm$ 25 mA
DC $V_{CC}$ or GND Current, per pin ( $I_{CC}$ )	$\pm$ 50 mA
Storage Temperature Range (T <sub>STG</sub> )	-65°C to +150°C

Power Dissipation (PD)

600 mW (Note 3) S.O. Package only 500 mW Lead Temp. (T<sub>L</sub>) (Soldering 10 seconds) 260°C

#### **Operating Conditions**

Min	Max	Units
2	12	V
0	$V_{CC}$	V
-40	+85	°C
-55	+125	°C
	1000	ns
	500	ns
	400	ns
	2 0 -40	2 12 0 V <sub>CC</sub> -40 +85 -55 +125 1000 500

#### **DC Electrical Characteristics** (Note 4)

Symbol	Parameter	Conditions	v <sub>cc</sub>	T <sub>A</sub> =25°C		74HC T <sub>A</sub> = -40 to 85°C	54HC T <sub>A</sub> = -55 to 125°C	Units
				Тур		Guaranteed Limits		
V <sub>IH</sub>	Minimum High Level		2.0V		1.5	1.5	1.5	٧
	Input Voltage		4.5V		3.15	3.15	3.15	V
			9.0V		6.3	6.3	6.3	V
			12.0V		8.4	8.4	8.4	V
$V_{IL}$	Maximum Low Level		2.0V		0.5	0.5	0.5	V
	Input Voltage**		4.5V		1.35	1.35	1.35	V
			9.0V		2.7	2.7	2.7	V
			12.0V		3.6	3.6	3.6	V
RON	Maximum 'ON' Resistance	V <sub>CTL</sub> = V <sub>IH</sub> , I <sub>S</sub> = 2.0 mA	4.5V	100	170	200	220	Ω
	(See Note 5)	V <sub>IS</sub> = V <sub>CC</sub> to GND	9.0V	50	85	105	120	Ω
		(Figure 1)	12.0V	30	70	85	100	Ω
			2.0V	100	180	215	240	Ω
		V <sub>CTL</sub> =V <sub>IH</sub> , I <sub>S</sub> =2.0 mA	4.5V	40	80	100	120	Ω
		V <sub>IS</sub> = V <sub>CC</sub> or GND	9.0V	35	60	75	80	Ω
		(Figure 1)	12.0V	20	40	60	70	Ω
RON	Maximum 'ON' Resistance	V <sub>CTL</sub> =V <sub>IH</sub>	4.5V	10	15	20	20	Ω
	Matching	V <sub>IS</sub> =V <sub>CC</sub> to GND	9.0V	5	10	15	15	Ω
R <sub>ON</sub>			12.V	5	10	15	15	Ω
I <sub>IN</sub>	Maximum Control Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		±0.1	±1.0	±1.0	μΑ
I <sub>IZ</sub>	Maximum Switch 'OFF'	V <sub>OS</sub> = V <sub>CC</sub> or GND	6.0V		±60	±600	±600	nA
	Leakage Current	V <sub>IS</sub> = GND or V <sub>CC</sub>	9.0V		±80	±800	±800	nA
		V <sub>CTL</sub> = V <sub>IL</sub> (Figure 2)	12.0V		±100	±1000	± 1000	nA
I <sub>IZ</sub>	Maximum Switch 'ON'	V <sub>IS</sub> =V <sub>CC</sub> to GND	6.0V		±40	± 150	±150	nA
	Leakage Current	V <sub>CTL</sub> = V <sub>IH</sub> , V <sub>OH</sub> = OPEN	9.0V		±50	±200	±200	nA
	-	(Figure 3)	12.0V		±60	±300	±300	nA
Icc	Maximum Quiescent	V <sub>IN</sub> = V <sub>CC</sub> or GND	6.0V		2.0	20	40	μΑ
. =	Supply Current	I <sub>OUT</sub> = 0 μA	9.0V		4.0	40	80	μA
			12.0V		8.0	80	160	μA

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 65°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V  $\pm$  10% the worst case on resistances (R<sub>ON</sub>) occurs for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V<sub>IH</sub> and V<sub>IL</sub> occur at V<sub>CC</sub>=5.5V and 4.5V respectively. (The V<sub>IH</sub> value at 5.5V is 3.85V.) The worst case leakage current occur for CMOS at the higher voltage and so these values should be used.

Note 5: At supply voltages (V<sub>CC</sub>-GND) approaching 2V the analog switch on resistance becomes extremely non-linear. Therefore it is recommended that these devices be used to transmit digital only when using these supply voltages.

<sup>\*\*</sup>V<sub>IL</sub> limits are currently tested at 20% of V<sub>CC</sub>. The above V<sub>IL</sub> specification (30% of V<sub>CC</sub>) will be implemented no later than Q1, CY'89.

AC Electrical Characteristics  $V_{CC} = 2.0V - 12.0V, C_L = 50 \ pF$  (unless otherwise specified), (Notes 6 and 7)

Symbol	Parameter	Conditions	v <sub>cc</sub>	T <sub>A</sub> =25°C		74HC T <sub>A</sub> = -40 to 85°C	54HC T <sub>A</sub> = -55 to 125°C	Units
				Тур		Guaranteed	•	
t <sub>PHL</sub> , t <sub>PLH</sub>	Maximum Propagation		2.0V	25	50	62	75	ns
	Delay Switch In to		4.5V	5	10	13	15	ns
	Out		9.0V	4	8	12	14	ns
			12.0V	3	7	11	13	ns
$t_{PZL},t_{PZH}$		$R_L = 1 k\Omega$	2.0V	32	100	125	150	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	"ON" Delay		4.5V	8	20	25	30	ns
			9.0V	6	12	15	18	ns
			12.0V	5	10	13	15	ns
$t_{PHZ}$ , $t_{PLZ}$	Maximum Switch Turn	$R_L = 1 k\Omega$	2.0V	45	168	210	252	ns
	"OFF" Delay		4.5V	15	36	45	54	ns
			9.0V	10	32	40	48	ns
			12.0V	8	30	38	45	ns
	Minimum Frequency	$R_L = 600\Omega, V_{IS} = 2V_{PP}$	4.5V	40				MHz
	Response (Figure 7)	at (V <sub>CC</sub> /2)	9.0V	100				MHz
	$20 \log (V_{OS}/V_{IS}) = -3 dB$	(Notes 6 & 7)						
	Control to Switch	$R_1 = 600\Omega$ , $F = 1 MHz$	4.5V	100				mV
	Feedthrough Noise	$C_L = 50  pF$	9.0V	250				mV
	(Figure 8)	(Notes 7 & 8)						
	Crosstalk Between	$R_{I} = 600\Omega, F = 1 MHz$						
	any Two Switches		4.5V	-52				dB
	(Figure 9)		9.0V	-50				dB
	Switch OFF Signal	$R_L = 600\Omega$ , $F = 1 MHz$						
	Feedthrough	$V_{CTL} = V_{IL}$						
	Isolation	(Notes 7 & 8)	4.5V	-42				dB
	(Figure 10)	(140103 7 & 0)	9.0V	-44				dB
THD	Sinewave Harmonic	$R_1 = 10 \text{ k}\Omega, C_1 = 50 \text{ pF},$						
וחט	Distortion	$ \mathbf{F}  = 10 \text{ k}_{2}, \text{ CL} = 50 \text{ pr},$ $ \mathbf{F}  = 1 \text{ kHz}$						
	(Figure 11)	$V_{IS} = 4V_{PP}$	4 5V	0.013				%
	(Figure 11)	$V_{IS} = 8V_{PP}$		0.008				%
	Maximum Cantral	113 2177			10	10	10	
C <sub>IN</sub>	Maximum Control Input Capacitance			5	10	10	10	pF
								<u> </u>
$C_{IN}$	Maximum Switch			15				pF
	Input Capacitance							
$C_{IN}$	Maximum Feedthrough	V <sub>CTL</sub> =GND		5				pF
	Capacitance							
C <sub>PD</sub>	Power Dissipation	(per switch)		15				pF
. 5	Capacitance	,						Ι΄.

Note 6: Adjust 0 dBm for F = 1 kHz (Null  $R_L/R_{\mbox{ON}}$  Attenuation)

Note 7:  $V_{\mbox{\scriptsize IS}}$  is centered at  $V_{\mbox{\scriptsize CC}}/2$ 

Note 8: Adjust input for 0 dBm

# **AC Test Circuits and Switching Time Waveforms**

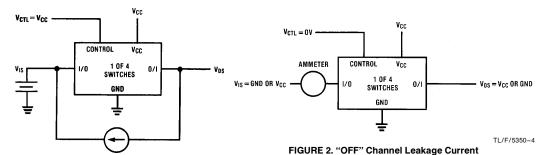


FIGURE 1. "ON" Resistance

AMMETER CONTROL VCC

1/0 1 OF 4
SWITCHES D/I
GND

VCC

Vos (OPEN)

TL/F/5350-5

FIGURE 3. "ON" Channel Leakage Current



FIGURE 4.  $t_{\text{PHL}}$ ,  $t_{\text{PLH}}$  Propagation Delay Time Signal Input to Signal Output

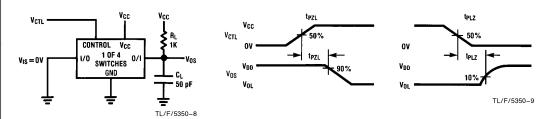


FIGURE 5.  $t_{\mbox{\scriptsize PZL}}, t_{\mbox{\scriptsize PLZ}}$  Propagation Delay Time Control to Signal Output

# AC Test Circuits and Switching Time Waveforms (Continued)

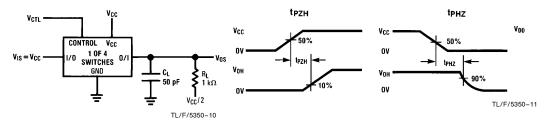


FIGURE 6.  $t_{\mbox{\scriptsize PZH}}, t_{\mbox{\scriptsize PHZ}}$  Propagation Delay Time Control to Signal Output

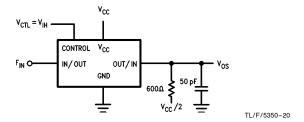


FIGURE 7. Frequency Response

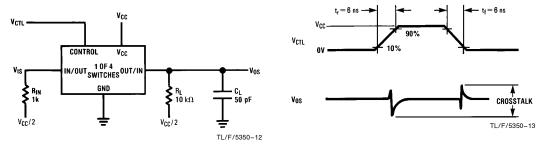
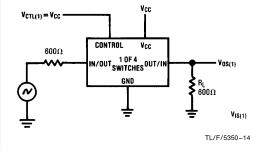
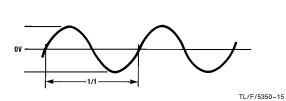


FIGURE 8. Crosstalk: Control Input to Signal Output

# AC Test Circuits and Switching Time Waveforms (Continued)





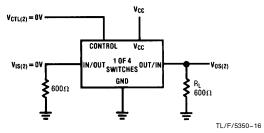


FIGURE 9. Crosstalk Between Any Two Switches

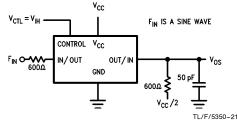


FIGURE 10. Switch OFF Signal Feedthrough Isolation

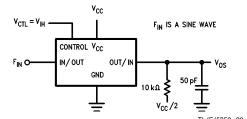
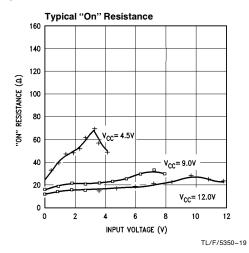
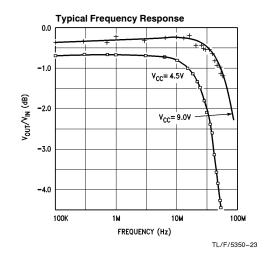


FIGURE 11. Sinewave Distortion

# **Typical Performance Characteristics**





TL/F/5350-24

Typical Crosstalk Between
Any Two Switches

-30

-40

V<sub>CC</sub>= 9.0V

V<sub>CC</sub>= 4.5V

-55

-60

-65

-70

100K

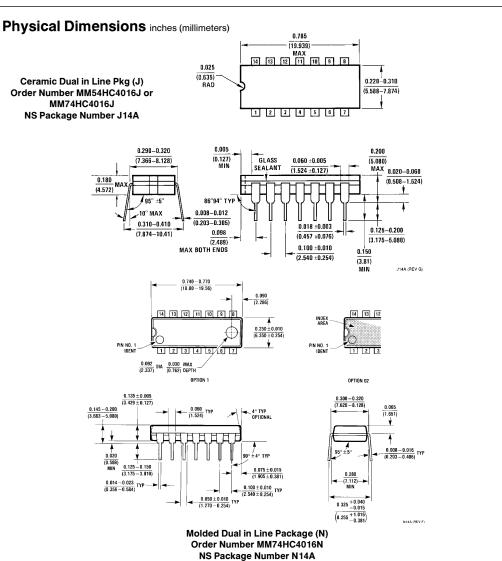
1M

100M

FREQUENCY (Hz)

#### **Special Considerations**

In certain applications the external load-resistor current may include both  $V_{CC}$  and signal line components. To avoid drawing  $V_{CC}$  current when switch current flows into the analog switch input pins, the voltage drop across the switch must not exceed 0.6V (calculated from the ON resistance).



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